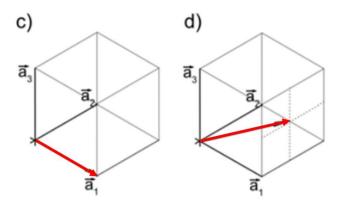
Assignment 2 Solutions:

Solution 1

For cubic systems

- a) We can see that the end of the vector is located at $\frac{1}{2}$ a1 + 1a2 + $\frac{1}{4}$ a3.
- b) We can convert this to a crystallographic direction by multiplying through by 4 to get rid of the fractions while preserving the ratios.

 The direction shown in a) is therefore [241].
- c) the end of the vector is located at $1a\sim2 + 1a\sim3$, which is represented as [011].
- c, d) Finally, the [100] (overlapping with a1 axis) and [211] directions are shown below:



For hexagonal systems

Determine 3-axis system [xyz] and then convert to 4-index [uvtw] system where

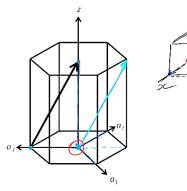
$$u = \frac{1}{3}(2x - y)$$

$$v = \frac{1}{3}(2y - x)$$

$$t = -(x + y)$$

$$w = z$$

a) First translate the vector to origin, (or translate the origin).



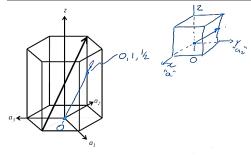
Now, [xyz] = [111]

Then,

$$u = \frac{1}{3}$$
, $v = \frac{1}{3}$, $t = -\frac{2}{3}$, $w = 1$

 $[uvtw] = [11\bar{2}3]$

First translate the vector to origin, (or translate the origin).



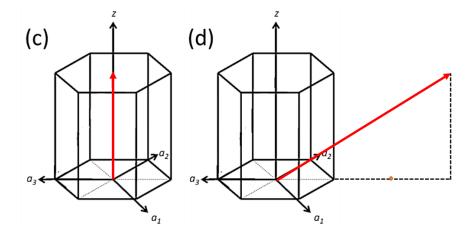
Now, [xyz] = [021]

Then,

$$u = -\frac{2}{3}$$
, $v = \frac{4}{3}$, $t = -\frac{2}{3}$, $w = 1$
[uvtw] = $[\overline{2}4\overline{2}3]$

c, d) [0001], $[11\overline{2}1]$ directions are shown below.

Same can be achieved by converting into 3-axis system and then plotting.



Solution 2

```
(i) n\lambda = 2d\sin\theta

n = 1, \theta = 14.35^{\circ}, \lambda = 0.071nm

h^2 + k^2 + l^2 = 8 is possible only for (hkl) = (220)

d = n\lambda/2\sin\theta

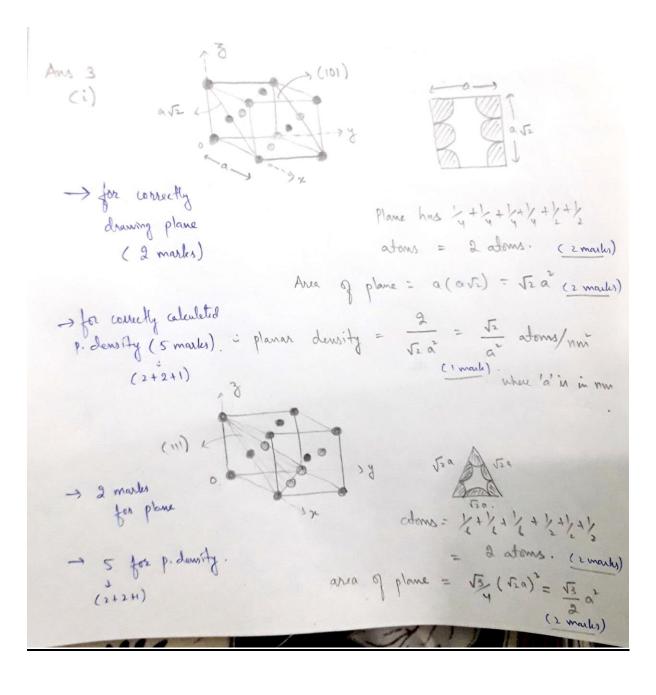
d = 0.071/2*\sin(14.35^{\circ}) = 0.071/0.4957 = 0.1432 nm

d = a/(\sqrt{h^2+k^2+l^2})

a = 0.1432*(2.828) = 0.405 nm = 0.405*(10^{-9}) m
```

- (ii) Reflections for smaller angle means large d and larger d means smaller $h^2+k^2+l^2$ (hkl) smaller than (220) are (200)- all even and (111)- all odd This means that the structure is FCC.
- (iii) Forbidden reflection for FCC is mixed odd and even.

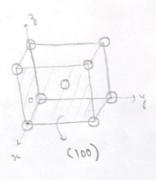
Solution 3



=> planae density =
$$\frac{2}{13/a^2} = \frac{4}{\sqrt{5}a^2}$$
 atms/

(mark).

Ams 3 (ii)



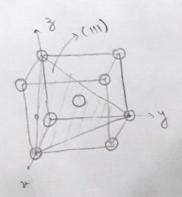
a Q

1/4 1/4 1/4 = conta p on

ona = 02.

planas density = - at atms/mm

(if 'a' is is nom).





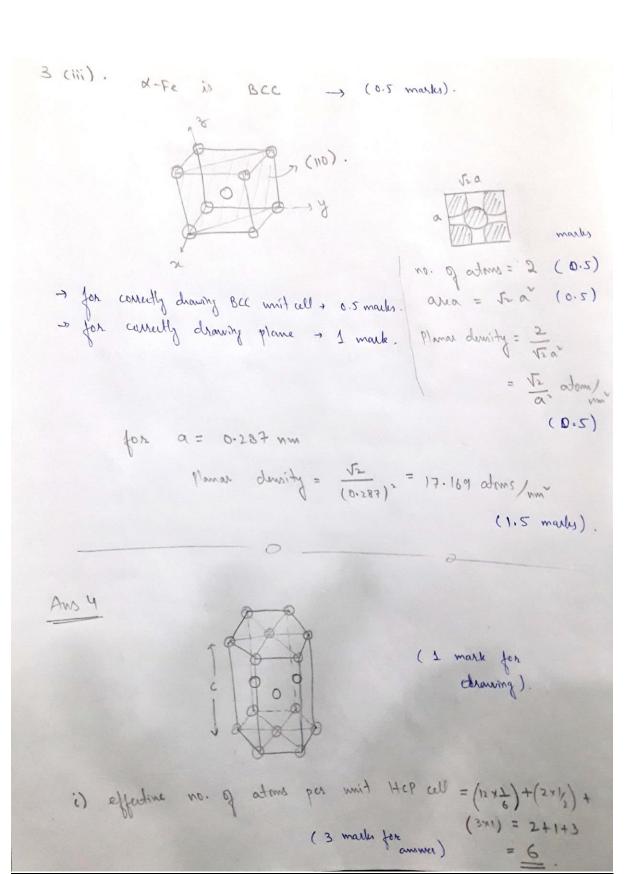
no. of atoms = 1/4/4 + 1/2 - 1/2.

area = 5/ (5/2) = 5/2 az

Planar density = 1/2 = 1/3 at aton/

-> Follow marking scheme as in partnerspart.

(if 'a' is in nm)



-> If some one has'n't explained a simply wither answer-

4 ii).



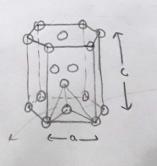
(I mark for drawing of showing parallelapiped

Herazarel primitive cell is 1/3 of prism, containing 8 corner atoms & 1 atom inside cell

i effective no. of atoms in parallelapiped unit cell of $HCP = 6 \times \frac{1}{3} = \frac{2}{2}$. (2 marks for right answer)

- if explanation missing - deduct 1 made.

4 (111).



$$\Rightarrow h + x = \alpha - (i)$$
where $h = \frac{4}{3}$.

$$x = \frac{\alpha/2}{\sqrt{3}/2}$$

$$x = \frac{\alpha}{\sqrt{3}/2}$$

$$\frac{c^{2}}{4} + \frac{a^{2}}{3} = a^{2}$$

$$\frac{2}{4} = \frac{2}{3}a^{2}$$

-> 5 marks for the complete answer.

4) iv). atmic parking fraction of their capital =

volume of adoms per unit cell

-> no. g atoms in parelleligided = 2 (as calculated carlier).

-> Volume of parellelepiped



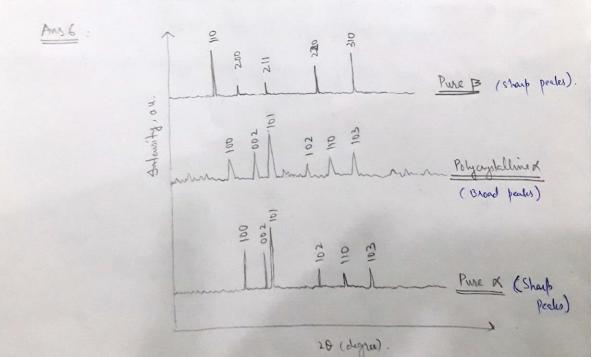


volume = axaxsin(120)xC

$$\frac{1}{2} \quad \text{parking furtion} = \frac{2 \times \sqrt[4]{7} \times 8^3}{8 \sqrt{5} \times 8^3} = \frac{1}{\sqrt{5} \times 3} = \frac{0.77}{10.3}$$

-> 3 marks for the question.

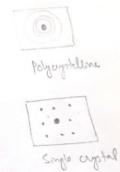
Note: Students may have calculated it differently. That is fine as long on they are doing it correctly.



-> Polycystolline meterial gives ring patterns
while single coystal samples yield 2-0 array
of spots.

In XXI Sharp peaks for single crystal are
seen while as in polycystolline broader

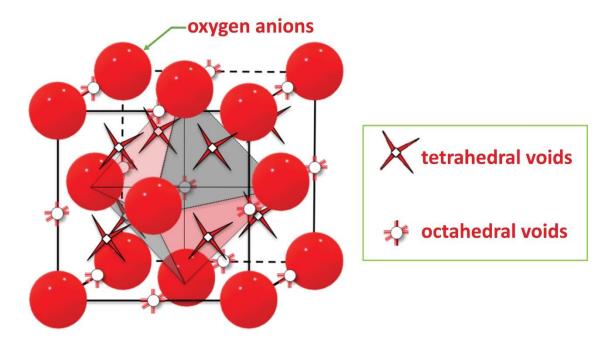
peaks are there.



- + X-Ti is HCP while B-Ti is BCC, so they will have different peaks in XRD.
- ⇒ Dearder 1.5 marks for drawing correctly XRD pattern 2 induring correctly XRD pattern 2 induring
 - ⇒ 0.5 for consetty highlighting the difference b/w polycystelline & single curital specimens.

Solution 5

In a cubic closed packing arrangement (CCP) of oxygen anions, we have



(a) No. of tetrahedral sites/unit cell = 1 * 8 = 8

No. of octahedral sites/unit cell = $\left(\frac{1}{4} \times 12 \text{ edge centres}\right) + (1 \times 1 \text{ body centre}) = 4$

(b) In a CCP arrangement of atoms, the number of octahedral sites is always equal to the number of atoms, while the number of tetrahedral sites is always double the number of atoms.

Here, the oxygen anions are in CCP arrangement. Thus the effective number of oxygen ions/unit cell = $\left(\frac{1}{2} \times 6 \text{ face centres}\right) + \left(\frac{1}{8} \times 8 \text{ cube corners}\right) = 4$ Therefore, the ratio of (octahedral sites : oxygen ions) = 4:4 = 1:1 and, the ratio of (tetrahedral sites : oxygen ions) = 8:4 = 2:1

(c) If one-half of the octahedral sites are filled with A,

then effective number of A/unit cell = $\left(\frac{1}{2} \times 4 \text{ octahedral voids}\right) = 2$

and since we already have 4 oxygen/unit cell, the stoichiometry of the oxide would be of the type $A_2O_4 \equiv AO_2$

If two-thirds of the octahedral sites are filled with A,

then effective number of A/unit cell = $\left(\frac{2}{3} \times 4 \text{ octahedral voids}\right) = \frac{8}{3}$ which is not a whole number. Hence, filling two-thirds of octahedral sites in a CCP arrangement is not possible.

[**Hint:** The 2/3rd occupancy in octahedral sites is only possible with hexagonal close- packed systems]

If all of the octahedral sites are filled with A,

then effective number of A/unit cell = $(1 \times 4 \ octahedral \ voids) = 4$ and since we already have 4 oxygen/unit cell, the stoichiometry of the oxide would be of the type $A_4O_4 \equiv AO$

(d) The coordinates of all the tetrahedral sites are:

$$\left(\frac{1}{4}, \frac{1}{4}, \frac{1}{4}\right) \left(\frac{3}{4}, \frac{1}{4}, \frac{1}{4}\right) \left(\frac{1}{4}, \frac{3}{4}, \frac{1}{4}\right) \left(\frac{3}{4}, \frac{3}{4}, \frac{1}{4}\right) \left(\frac{1}{4}, \frac{1}{4}, \frac{3}{4}\right) \left(\frac{3}{4}, \frac{1}{4}, \frac{3}{4}\right) \left(\frac{1}{4}, \frac{3}{4}, \frac{3}{4}\right) \left(\frac{3}{4}, \frac{3}{4}, \frac{3}{4}\right) \left(\frac$$

Assuming a cation 'M' to be filled into the tetrahedral sites. Filling all the tetrahedral sites, we have then

effective number of M/unit cell = $(1 \times 8 \text{ tetrahedral voids}) = 8$ and since we already have 4 oxygen/unit cell, the stoichiometry of the oxide would be of the type $M_8O_4 \equiv M_2O$ (Antifluorite structure) In order to preserve the charge neutrality, the effective charge of the crystal should be nullified. Hence, $2x + 1(-2) = 0 \implies x = +1$

Therefore, the cation M has to be monovalent, e.g. Li⁺, Na⁺, K⁺, Rb⁺

(e) The coordinates of all the octahedral sites are:

Assuming a cation 'M' to be filled into the octahedral sites. Filling all the octahedral sites, we have then

effective number of M/unit cell = $(1 \times 4 \text{ octahedral voids}) = 4$ and since we already have 4 oxygen/unit cell, the stoichiometry of the oxide would be of the type $M_4O_4 \equiv MO$ (**Rock salt structure**)

In order to preserve the charge neutrality, the effective charge of the crystal should be nullified. Hence, $1(x) + 1(-2) = 0 \implies x = +2$

Therefore, the cation M has to be divalent, e.g. Mg^{2+} , Ca^{2+} , Sr^{2+} , Ba^{2+}